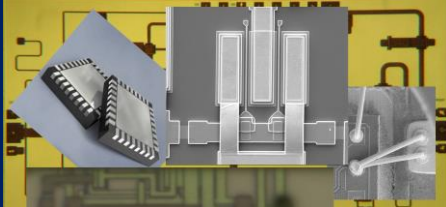


TMC200

DC-18 GHz

Distributed Amplifier



Product Features

- RF frequency: DC to 18 GHz
- Linear Gain: 17 dB
- Psat: 2 W
- Die Size: X=2.5 mm, Y=2 mm
- 0.15um GaAs PHEMT Process
- 2 mil GaAs substrate
- DC Power: 12 VDC, 250 mA

Application

- Point-to-Point Radios and VSATs
- Test instrumentation
- Fiber Optics
- Military, EW and Space

Product Description

The TMC200 GaAs PHEMT Distributed amplifier is a broadband device, designed for use in Radios, Test instrumentation, Military, EW and Space applications. The TMC200 is a 50 Ω matched design which eliminates the need for RF port matching. To ensure rugged and reliable operation and moisture protection, the TMC200 is fully passivated. Both bond pad and backside metallization are Au-based that is compatible with ribbon and wedge bonding and high conductivity epoxy and eutectic die attach methods.

Electrical Performance : Vdd = 12 V, Vgg = -1.0 V, TA = 25 °C, F = 10 GHz

	min	Typ	Max	Units
Frequency	DC		18	GHz
Gain		17		dB
P1dB		30		dBm
Psat		33		dBm
Noise Figure		3		dB
OIP3		41		dBm
Bias Voltage		12		V
Bias Current		250		mA

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